

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
30V	$73\text{m}\Omega$ @ $V_{GS} = 10\text{V}$	3.3A
	$110\text{m}\Omega$ @ $V_{GS} = 4.5\text{V}$	2.7A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at
<https://www.diodes.com/products/automotive/automotive-products/>.
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
<https://www.diodes.com/quality/product-definitions/>

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

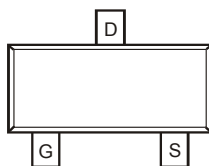
- General Purpose Interfacing Switch
- Power Management Functions
- Boost Application
- Analog Switch

Mechanical Data

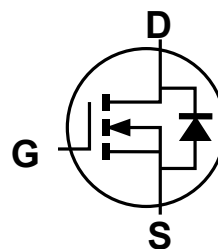
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish—Matte Tin Annealed Over Copper Lead-Frame.
Solderable per MIL-STD-202, Method 208 
- Weight: 0.027 grams (approximate)



Top View



Pin Configuration



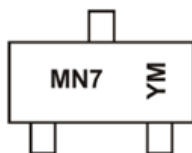
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3110S-7	SOT23	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



MN7 = Product Type Marking Code
 YM = Date Code Marking
 Y or $\bar{Y}$ = Year (ex: I = 2021)
 M = Month (ex: 9 = September)

Date Code Key

Year	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	I	J	K	L	M	N	O	P	R	S	T	U

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DS}	30	V
Gate-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	2.5 2.0	A
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	3.3 2.7	A
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	$t \leq 10\text{sec}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	3.8 3.1	A
Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	2.7 2.1	A
Pulsed Drain Current (Note 7)			I_{DM}	25	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

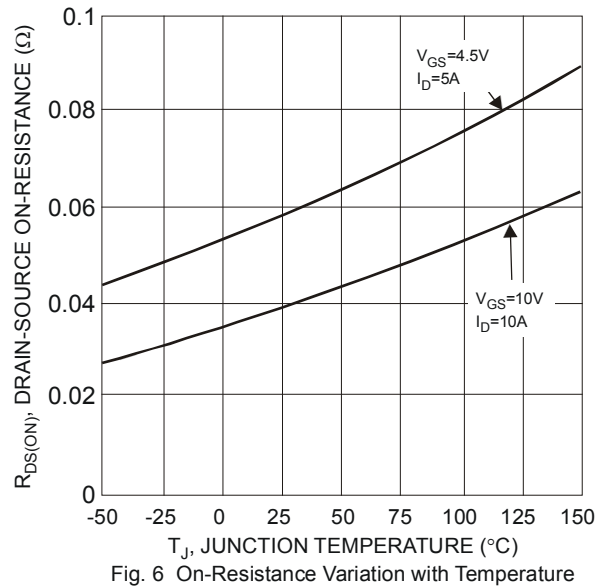
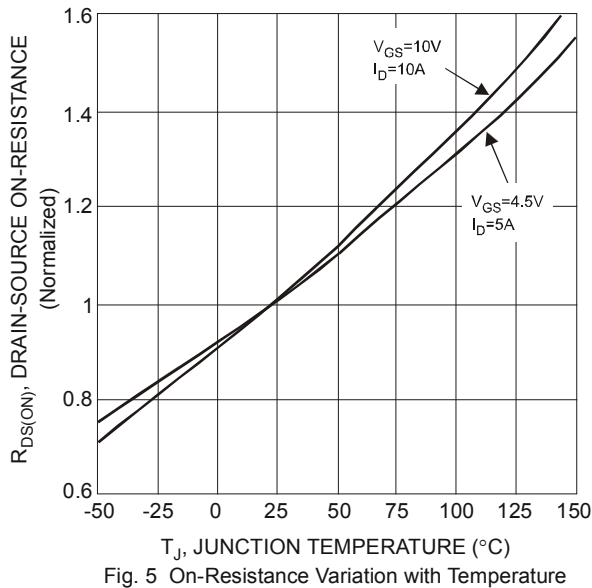
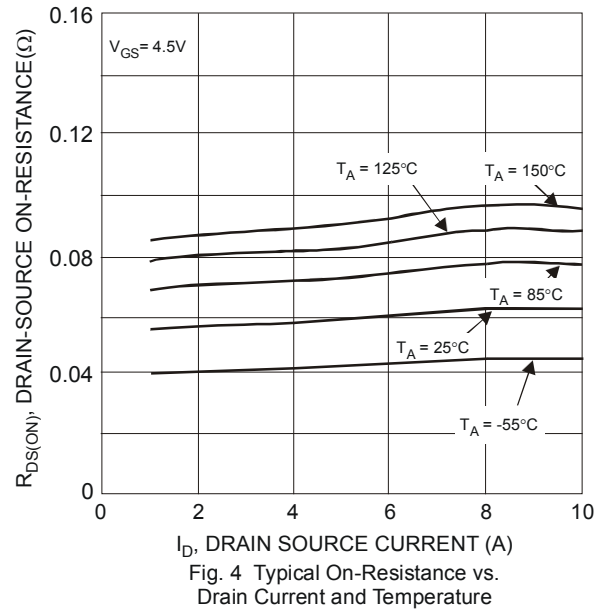
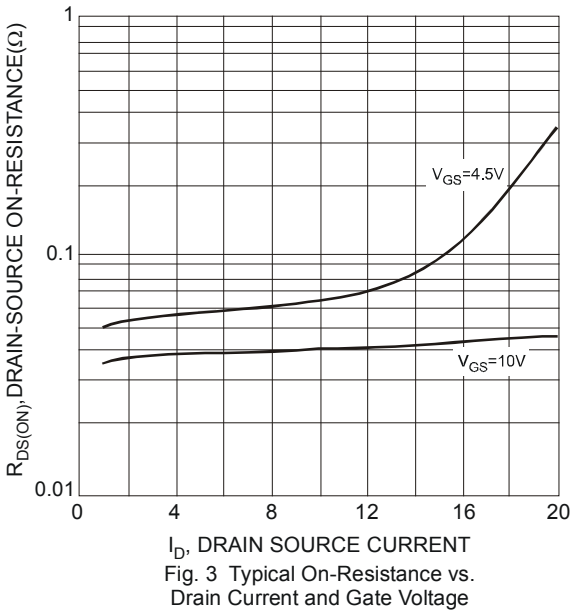
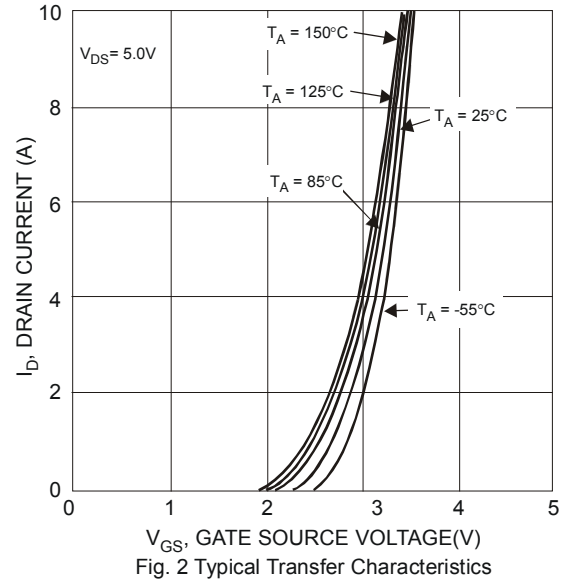
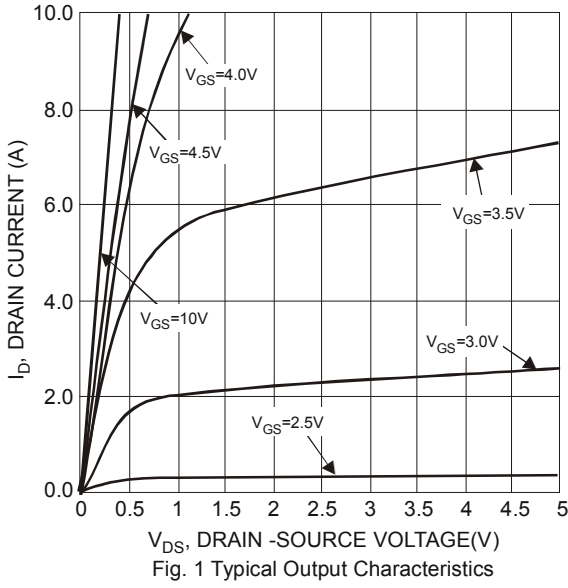
Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	0.74	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	173.4	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)	P_D	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	99.1	$^\circ\text{C/W}$
Total Power Dissipation (Note 6) $t \leq 10\text{sec}$	P_D	1.8	W
Thermal Resistance, Junction to Ambient (Note 6) $t \leq 10\text{sec}$	$R_{\theta JA}$	72	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, on 1inch square copper plate
 7. Device mounted on minimum recommended pad layout test board, 10 μs pulse duty cycle = 1%

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current @ $T_C = +25^\circ\text{C}$	I_{DSS}	-	-	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	-	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	-	54	73	m Ω	$V_{GS} = 10V, I_D = 3.1A$
		-	88	110		$V_{GS} = 4.5V, I_D = 2A$
Forward Transfer Admittance	$ Y_{fs} $	-	4.8	-	mS	$V_{DS} = 10V, I_D = 3.1A$
Diode Forward Voltage (Note 6)	V_{SD}	-	0.75	1.0	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	-	305.8	-	pF	$V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz$
Output Capacitance	C_{oss}	-	39.9	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	39.5	-	pF	
Gate Resistance	R_g	-	1.4	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge ($V_{GS} = 4.5V$)	Q_g	-	4.1	-	nC	$V_{GS} = 10V, V_{DS} = 10V, I_D = 3A$
Total Gate Charge ($V_{GS} = 10V$)	Q_g	-	8.6	-	nC	
Gate-Source Charge	Q_{gs}	-	1.2	-	nC	
Gate-Drain Charge	Q_{gd}	-	1.5	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	2.6	-	ns	$V_{DD} = 15V, V_{GS} = 10V, R_L = 47\Omega, R_G = 3\Omega,$
Turn-On Rise Time	t_r	-	4.6	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	13.1	-	ns	
Turn-Off Fall Time	t_f	-	2.5	-	ns	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.



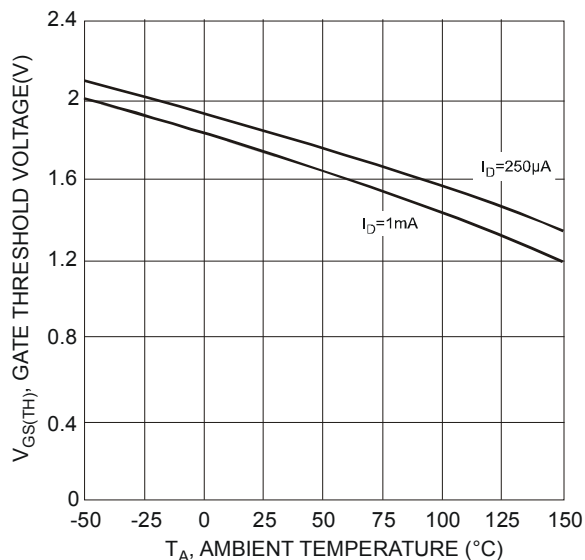


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

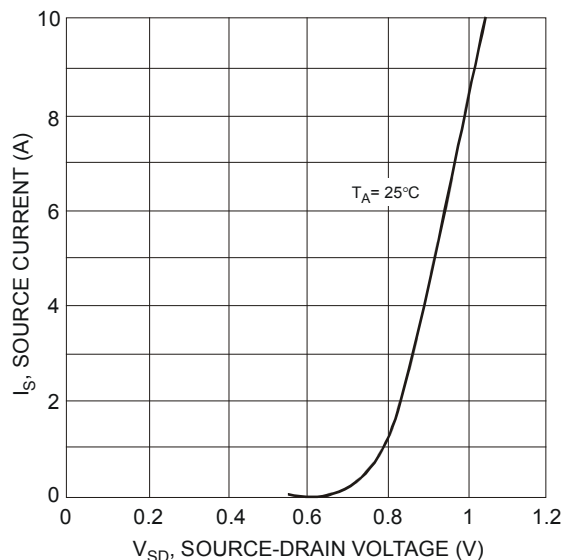


Fig. 8 Diode Forward Voltage vs. Current

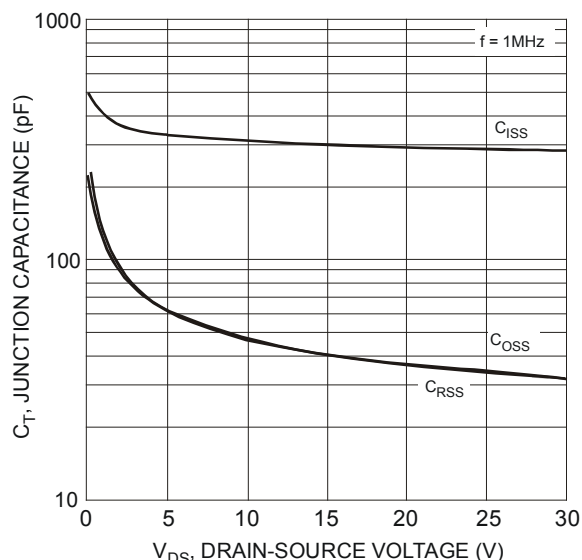


Fig. 9 Typical Junction Capacitance

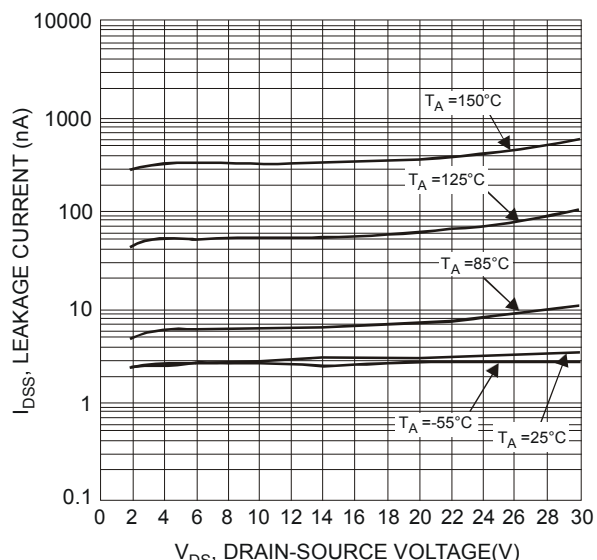


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

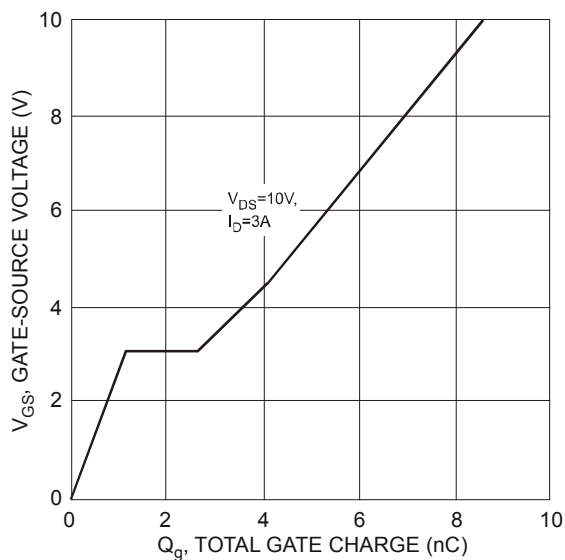
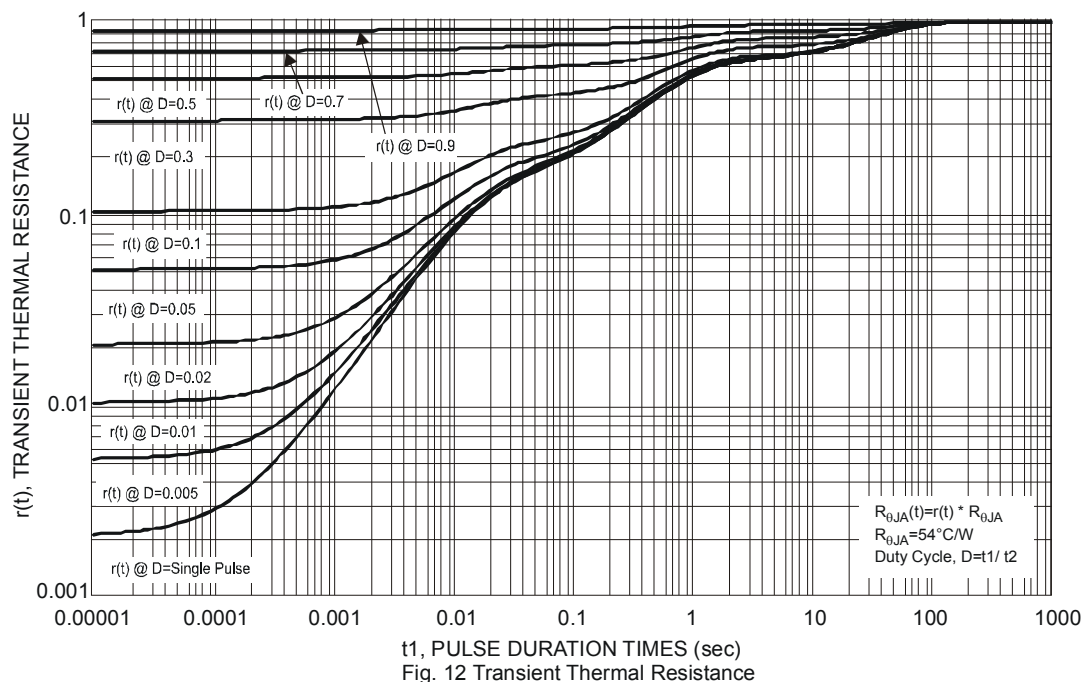


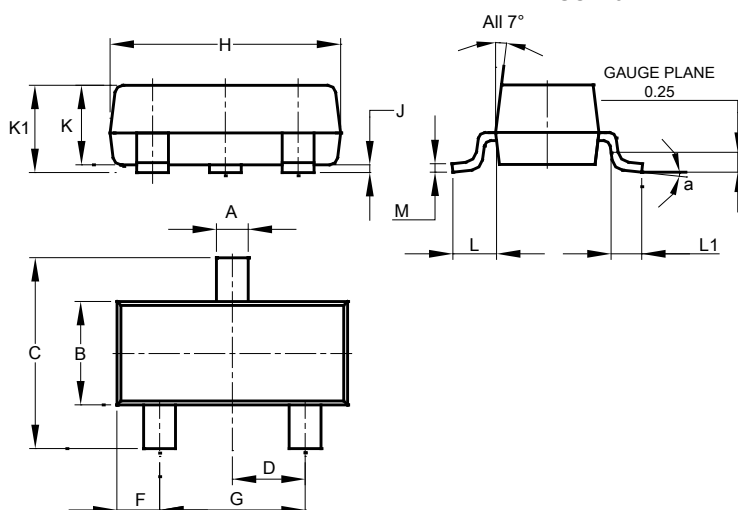
Fig. 11 Gate-Charge Characteristics



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

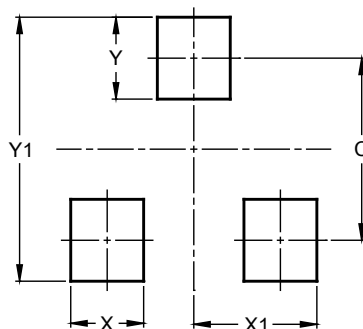


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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